



Description

The HAONR21321 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -30V$ $I_D = -50A$

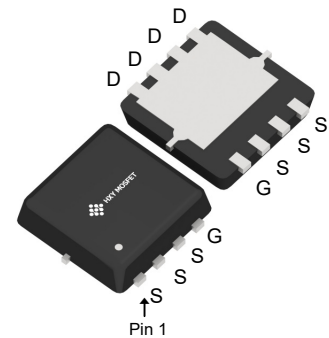
$R_{DS(ON)} < 13m\Omega$ @ $V_{GS} = -10V$

Application

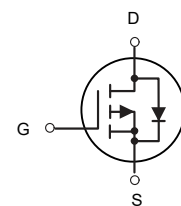
Battery protection

Load switch

Uninterruptible power supply



DFN3X3-8L



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HAONR21321	DFN3X3-8L	HXY MOSFET	5000

Absolute Maximum Ratings (TC=25°C unless otherwise specified)

Symbol	Parameter	Rating		Units
		10s	Steady State	
VDS	Drain-Source Voltage	-30		V
VGS	Gate-Source Voltage	±20		V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-50		A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-27		A
IDM	Pulsed Drain Current	-130		A
EAS	Single Pulse Avalanche Energy ³	125		mJ
IAS	Avalanche Current	-50		A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	37		W
TSTG	Storage Temperature Range	-55 to 150		°C
T _J	Operating Junction Temperature Range	-55 to 150		°C
R _{θJA}	Thermal Resistance Junction-Ambient ¹	75		°C/W
R _{θJA}	Thermal Resistance Junction-Ambient ¹ (t ≤ 10s)	30		°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	3.36		°C/W



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

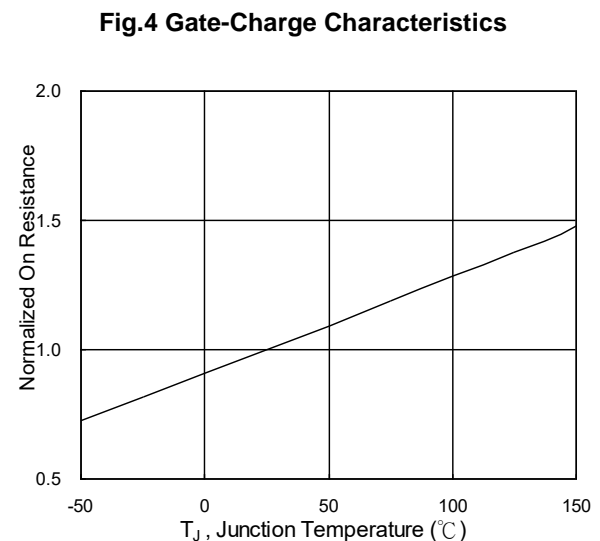
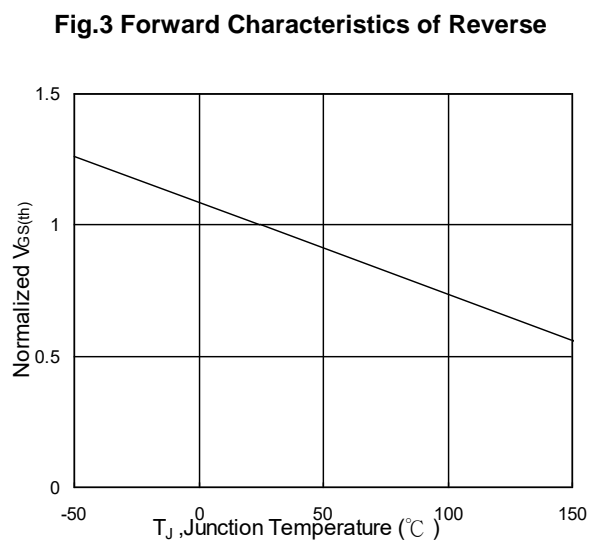
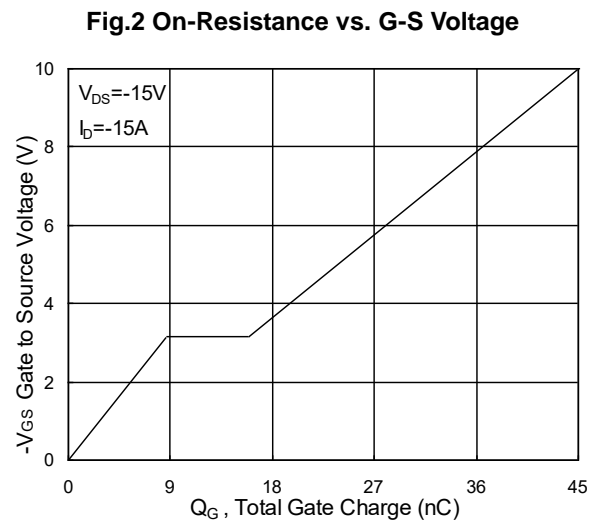
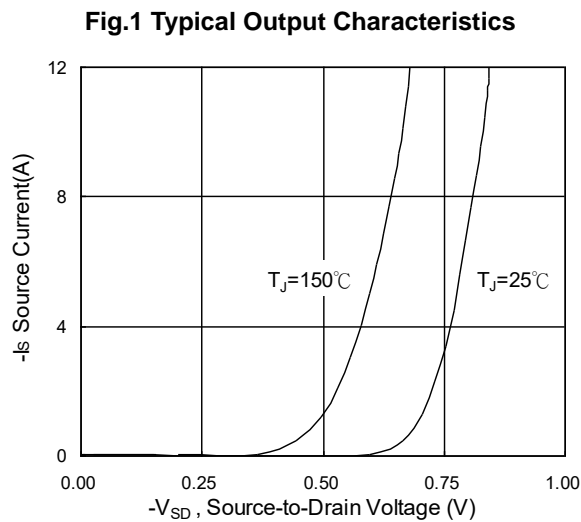
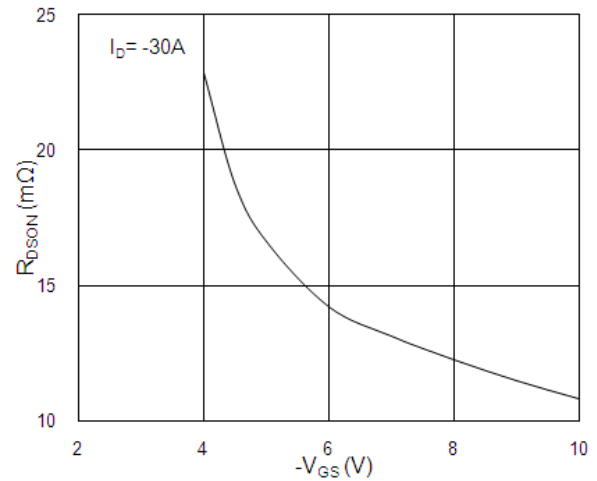
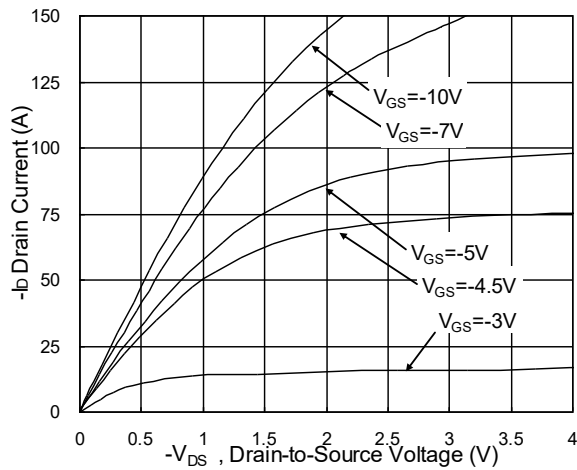
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.0232	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-30A$	---	9	13	$m\Omega$
		$V_{GS}=-4.5V$, $I_D=-15A$	---	16	22	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.2	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.6	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-5V$, $I_D=-30A$	---	30	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	9	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V$, $V_{GS}=-4.5V$, $I_D=-15A$	---	22	---	nC
Q_{gs}	Gate-Source Charge		---	8.7	---	
Q_{gd}	Gate-Drain Charge		---	7.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$, $V_{GS}=-10V$, $R_G=3.3$, $I_D=-15A$	---	8	---	ns
T_r	Rise Time		---	73.7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	61.8	---	
T_f	Fall Time		---	24.4	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2215	---	pF
C_{oss}	Output Capacitance		---	310	---	
C_{rss}	Reverse Transfer Capacitance		---	237	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-42	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-130	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1	V
t_{rr}	Reverse Recovery Time	$I_F=-15A$, $dI/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	19	---	nS
Q_{rr}	Reverse Recovery Charge		---	9	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$ duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V$ $V_{GS}=-10V$, $L=0.1mH$, $I_{AS}=-50A$,
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics



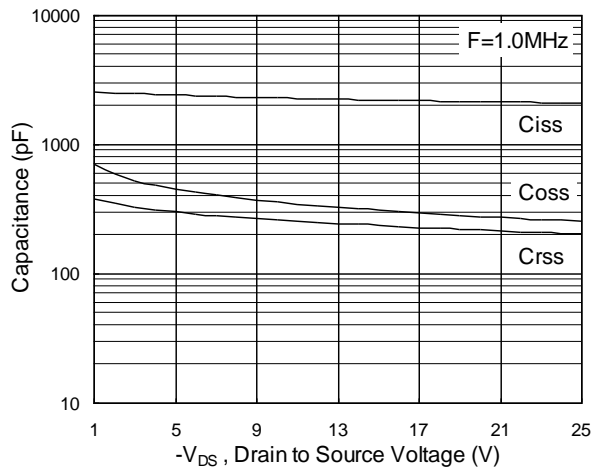


Fig.7 Capacitance

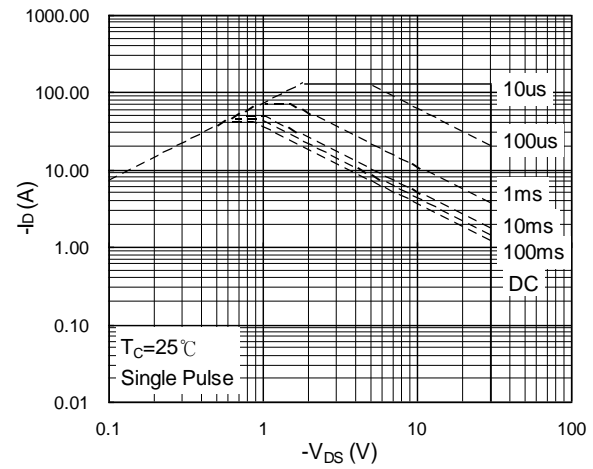


Fig.8 Safe Operating Area

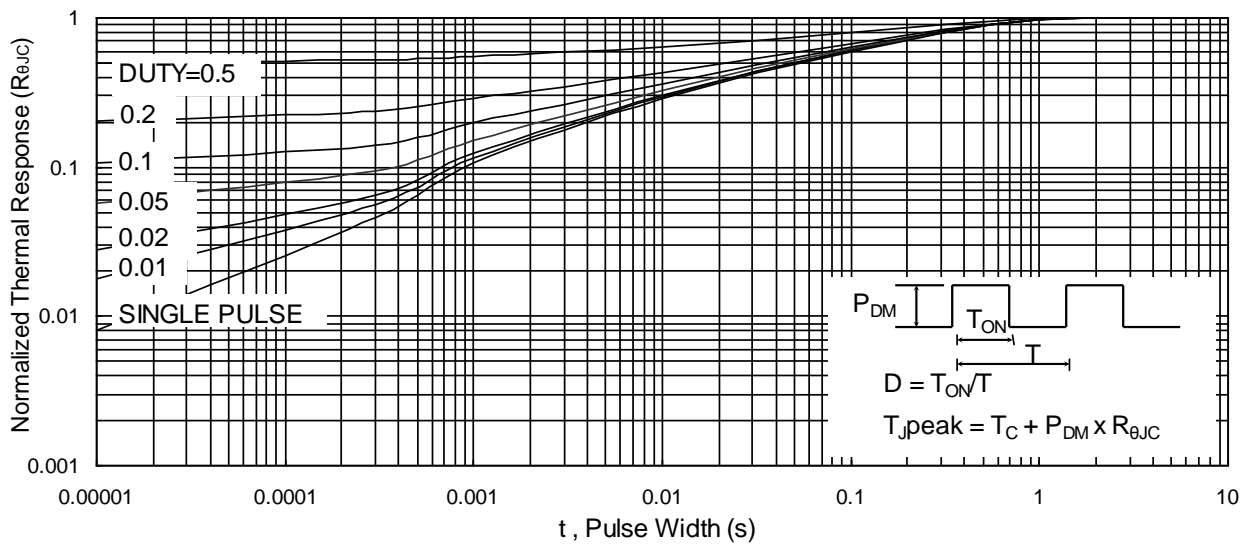


Fig.9 Normalized Maximum Transient Thermal Impedance

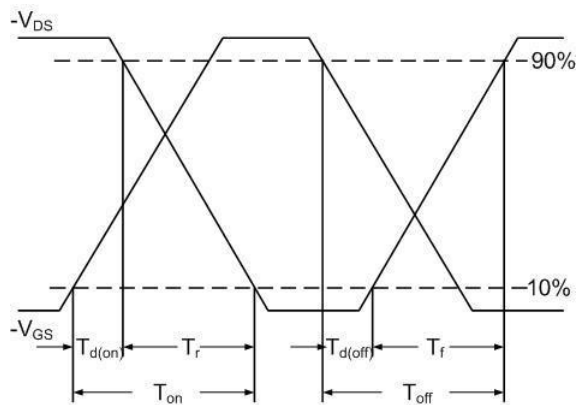


Fig.10 Switching Time Waveform

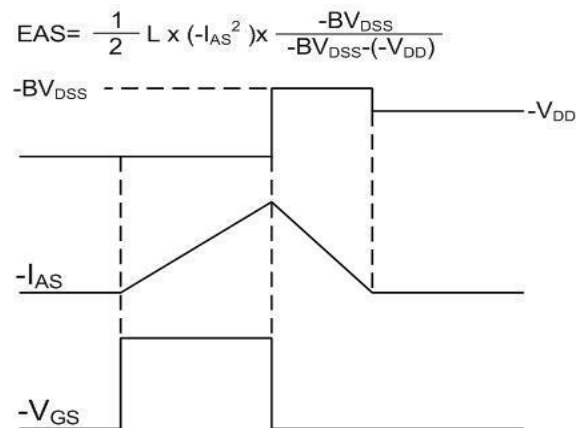
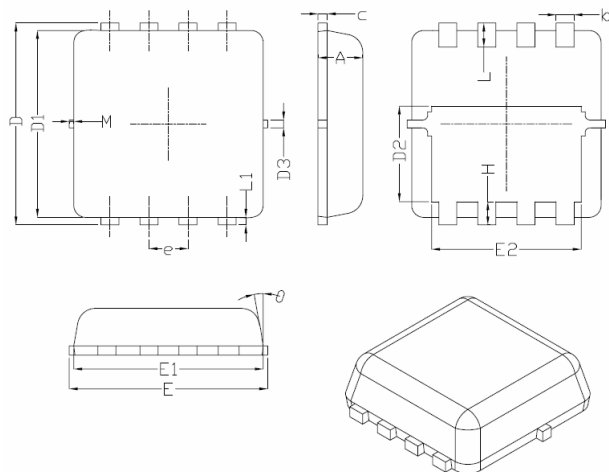


Fig.11 Unclamped Inductive Switching Waveform



DFN3X3-8L Package Information



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°



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